Description

This 100V 50A N-Channel MOSFET in a PDFN5×6 Plastic Package .

Features

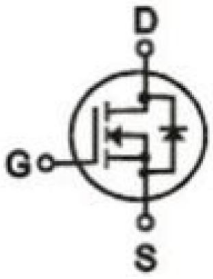
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low gate charge for fast switching
- Low thermal resistance
- Halogen-free product

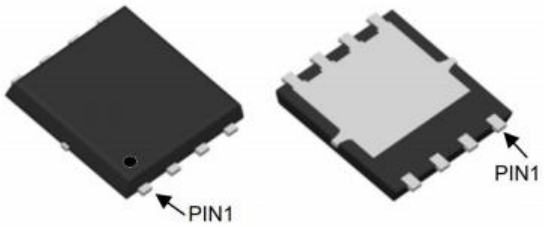
Applications

- For boost converters and synchronous rectifiers for consumer
- Telecom
- Industrial power supplies and LED backlighting

V_{DSS}	$R_{DS(ON)(typ)}$	I_D
100 V	6.7 mΩ	50A

Equivalent Circuit & Pinning





PIN1、2、3： S　　PIN4：G　　PIN5、6、7、8：D

Pin	极性
1	S
2	S
3	S
4	G
5	D
6	D
7	D
8	D

Marking

See Marking Instructions

Absolute Maximum Ratings(Ta=25℃)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Drain Current - Continuous		I_D	50	A
Drain Current – Pulsed		I_{DM}	200	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		$P_D(T_c=25℃)$	48	W
Single Pulse Avalanche Energy(L=0.5mH)		E_{AS}	119	mJ
Avalanche Current(L=0.5mH)		I_{AS}	18.5	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	℃
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	25	℃/ W
	Steady-State		55	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	2.6	

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA, V_{GS}=0V	100	109		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100V, V_{GS}=0V			1.0	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	2	2.9	4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=30A		6.7	8	mΩ
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		2500		pF
Output Capacitance	C_{oss}			1250		
Reverse Transfer Capacitance	C_{rss}			110		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V f=1MHz		3.1		Ω
Total Gate Charge	Q_g	V_{GS}=10V, V_{DS}=50V I_D=20A		25		nC
Gate Source Charge	Q_{gs}			6		
Gate Drain Charge	Q_{gd}			3.5		

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DS}=50V, R_L=2.5Ω, R_{GEN}=3Ω		8.5		ns
Turn-On Rise Time	t_r			3		
Turn-Off Delay Time	$t_{D(off)}$			23		
Turn-Off Fall Time	t_f			3.5		

Electrical Characteristic Curve

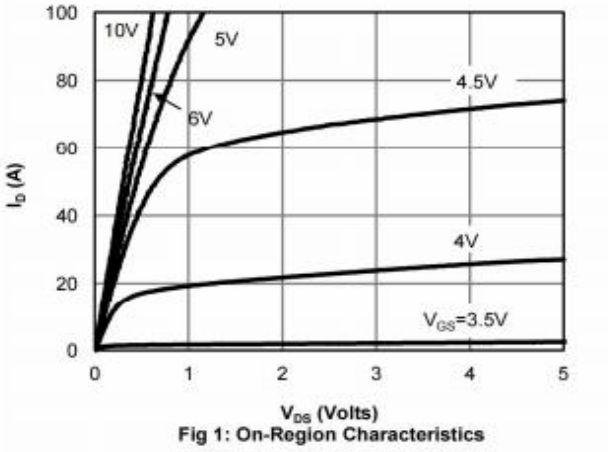


Fig 1: On-Region Characteristics

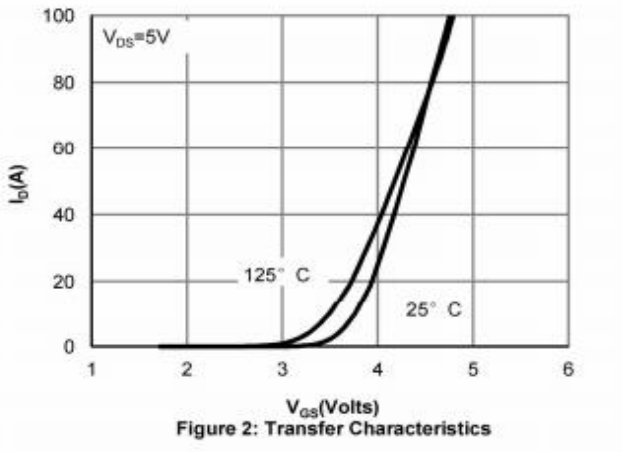


Figure 2: Transfer Characteristics

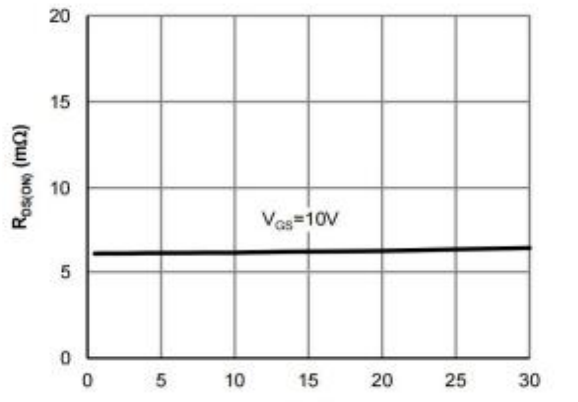


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

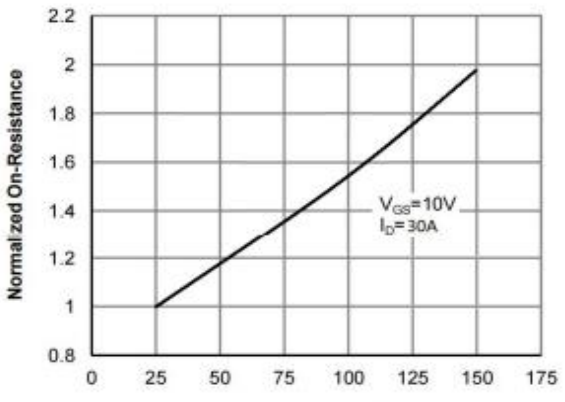


Figure 4: On-Resistance vs. Junction Temperature

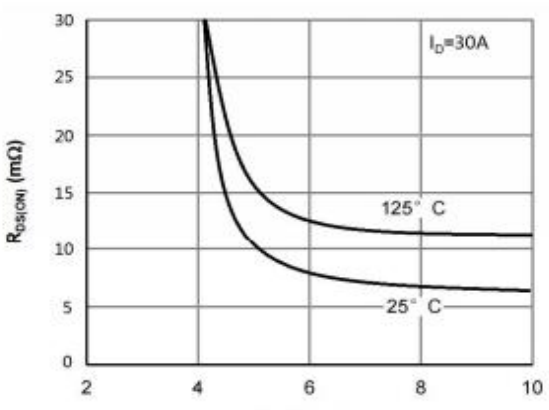


Figure 5: On-Resistance vs. Gate-Source Voltage

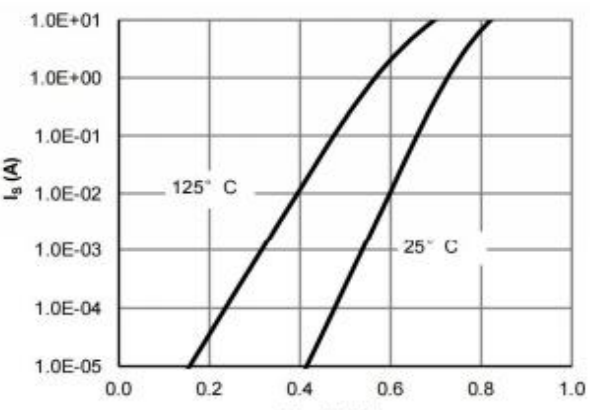


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

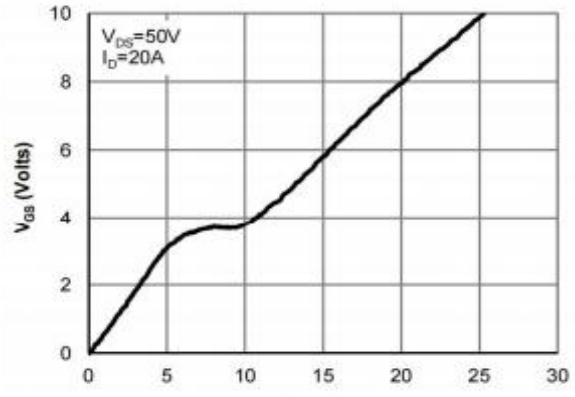


Figure 7: Gate-Charge Characteristics

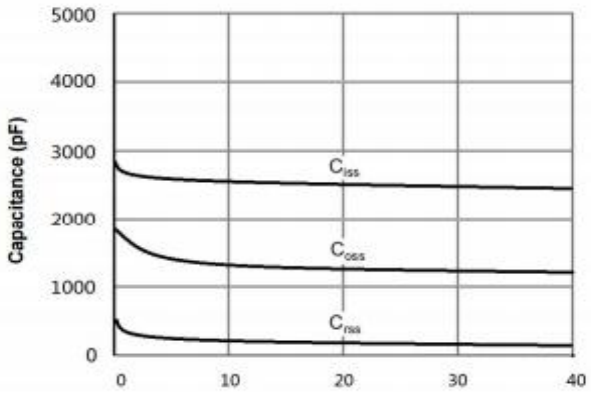


Figure 8: Capacitance Characteristics

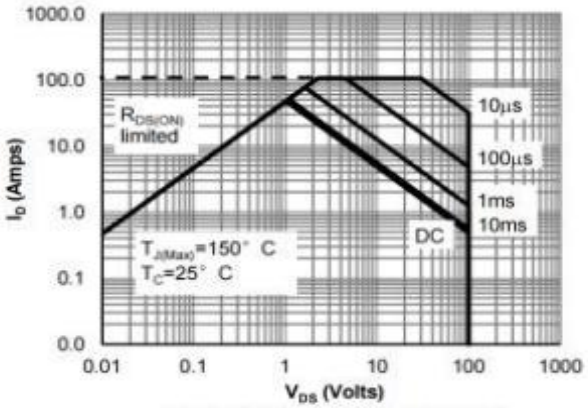


Figure 9: Maximum Forward Biased Safe Operating Area

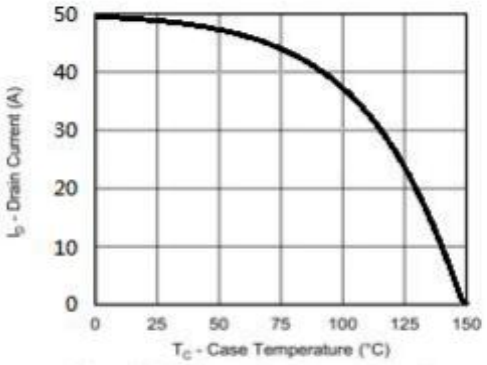


Figure10. Maximum Continuous Drain Current vs Case Temperature

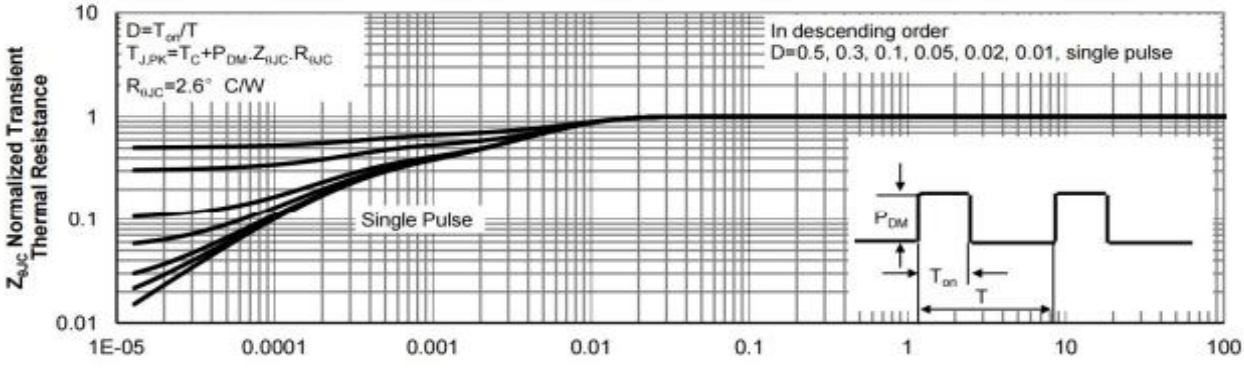
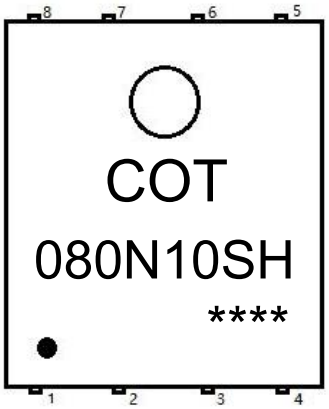


Figure 11: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Code

080N10SH: Product Type

****: Lot No. Code, code change with Lot No

Packaging SPEC

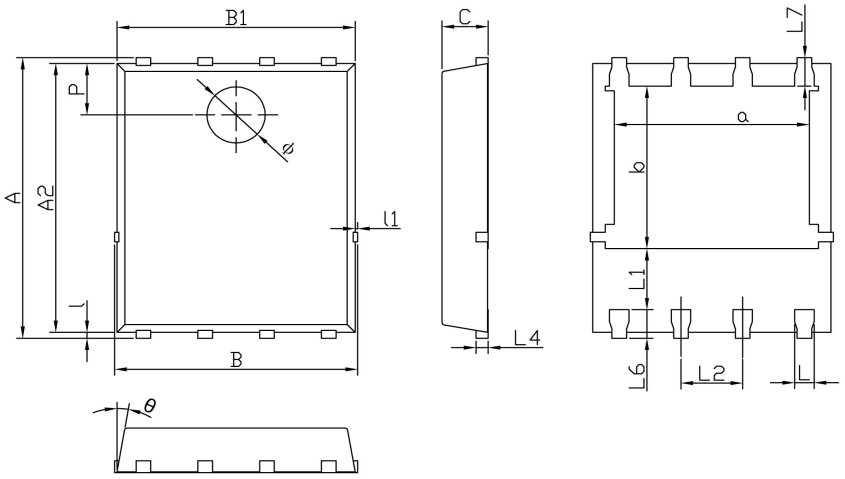
REEL

Package Type	Units					Dimension (unit: mm³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5×6	5000	2	10000	6	60000	13''×12	360×360×50	380×335×366

Package Outline Dimensions

PDFN5×6

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	–	–
l1	–	–	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
Φ	1.10	1.20	1.30

Rev.00 201812